

**Features :**

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

| $V_{DSM}, V_{RSM}$ | $V_{DRM}, V_{RRM}$ | Type       |
|--------------------|--------------------|------------|
| 2100V              | 2000V              | Mx250TH200 |
| 2300V              | 2200V              | Mx250TH220 |
| 2600V              | 2500V              | Mx250TH250 |

| SYMBOL                 | CHARACTERISTIC                             | TEST CONDITIONS                                                   | $T_j(^{\circ}C)$ | VALUE |      |      | UNIT              |
|------------------------|--------------------------------------------|-------------------------------------------------------------------|------------------|-------|------|------|-------------------|
|                        |                                            |                                                                   |                  | Min   | Type | Max  |                   |
| $I_{T(AV)}$            | Mean on-state current                      | 180° half sine wave 50Hz<br>Single side cooled, $T_c=85^{\circ}C$ | 125              |       |      | 250  | A                 |
| $I_{T(RMS)}$           | RMS on-state current                       |                                                                   |                  |       |      | 393  | A                 |
| $I_{DRM}$<br>$I_{RRM}$ | Repetitive peak current                    | at $V_{DRM}$<br>at $V_{RRM}$                                      | 125              |       |      | 30   | mA                |
| $I_{TSM}$              | Surge on-state current                     | 10ms half sine wave                                               | 125              |       |      | 9.0  | kA                |
| $I^2t$                 | $I^2t$ for fusing coordination             | $V_R=60\%V_{RRM}$                                                 |                  |       |      | 405  | $A^2s \cdot 10^3$ |
| $V_{TO}$               | Threshold voltage                          |                                                                   | 125              |       |      | 0.85 | V                 |
| $r_T$                  | On-state slope resistance                  |                                                                   |                  |       |      | 0.80 | m $\Omega$        |
| $V_{TM}$               | Peak on-state voltage                      | $I_{TM}=750A$                                                     | 25               |       |      | 1.73 | V                 |
| $dv/dt$                | Critical rate of rise of off-state voltage | $V_{DM}=67\%V_{DRM}$                                              | 125              |       |      | 1000 | V/ $\mu$ s        |
| $di/dt$                | Critical rate of rise of on-state current  | Gate source 1.5A<br>$t_r \leq 0.5\mu$ s Repetitive                | 125              |       |      | 200  | A/ $\mu$ s        |
| $I_{GT}$               | Gate trigger current                       | $V_A=12V, I_A=1A$                                                 | 25               | 30    |      | 180  | mA                |
| $V_{GT}$               | Gate trigger voltage                       |                                                                   |                  | 0.8   |      | 2.5  | V                 |
| $I_H$                  | Holding current                            |                                                                   |                  | 20    |      | 150  | mA                |
| $V_{GD}$               | Non-trigger gate voltage                   | $V_{DM}=67\%V_{DRM}$                                              | 125              | 0.2   |      |      | V                 |
| $R_{th(j-c)}$          | Thermal resistance<br>Junction to case     | Single side cooled per chip                                       |                  |       |      | 0.12 | $^{\circ}C/W$     |
| $R_{th(c-h)}$          | Thermal resistance<br>case to heat sink    | Single side cooled per chip                                       |                  |       |      | 0.04 | $^{\circ}C/W$     |
| $V_{iso}$              | Isolation voltage                          | 50Hz, R.M.S, $t=1min, I_{iso}: 1mA(MAX)$                          |                  | 3000  |      |      | V                 |
| $F_m$                  | Terminal connection torque (M8)            |                                                                   |                  |       | 12.0 |      | N·m               |
|                        | Mounting torque (M6)                       |                                                                   |                  |       | 6.0  |      | N·m               |
| $T_{vj}$               | Junction temperature                       |                                                                   |                  | -40   |      | 125  | $^{\circ}C$       |
| $T_{stg}$              | Stored temperature                         |                                                                   |                  | -40   |      | 125  | $^{\circ}C$       |
| $W_t$                  | Weight                                     |                                                                   |                  |       | 810  |      | g                 |
| Outline                | M03                                        |                                                                   |                  |       |      |      |                   |

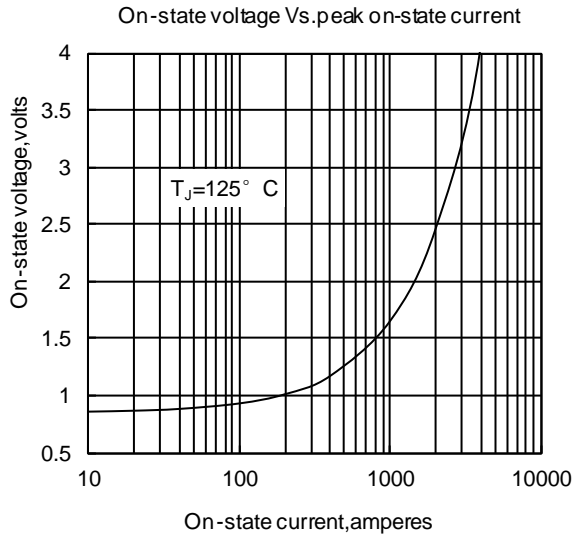


Fig. 1

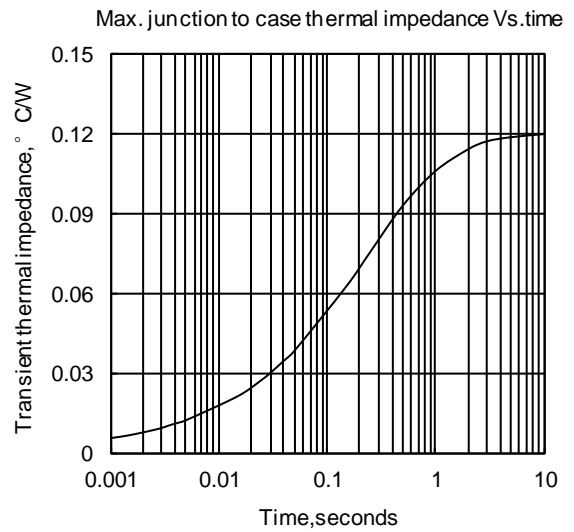


Fig. 2

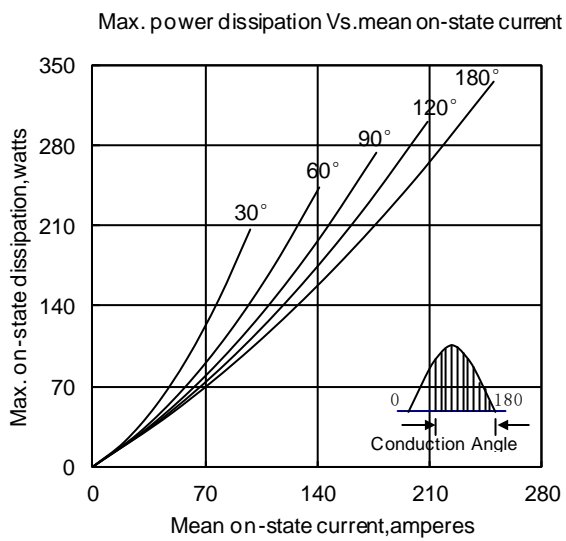


Fig. 3

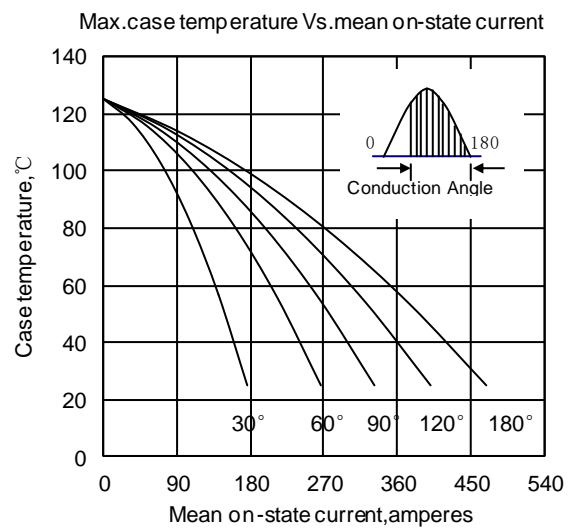


Fig. 4

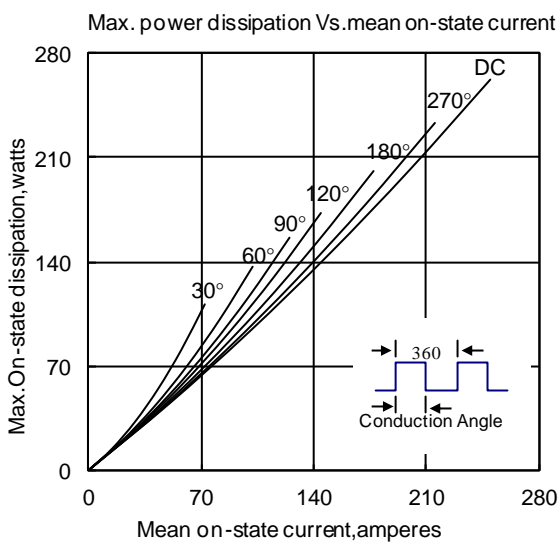


Fig. 5

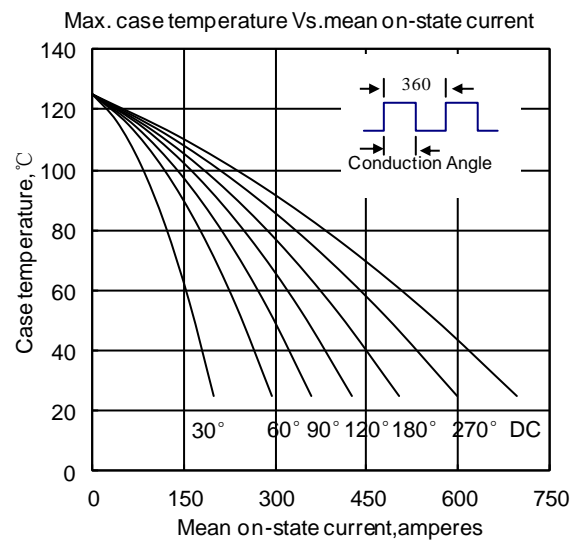


Fig. 6

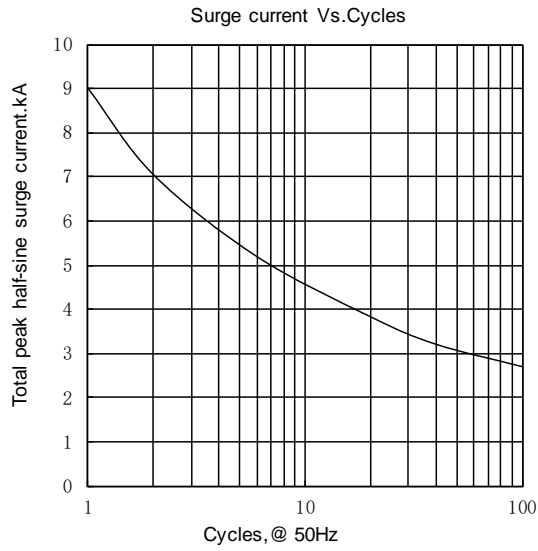


Fig.7

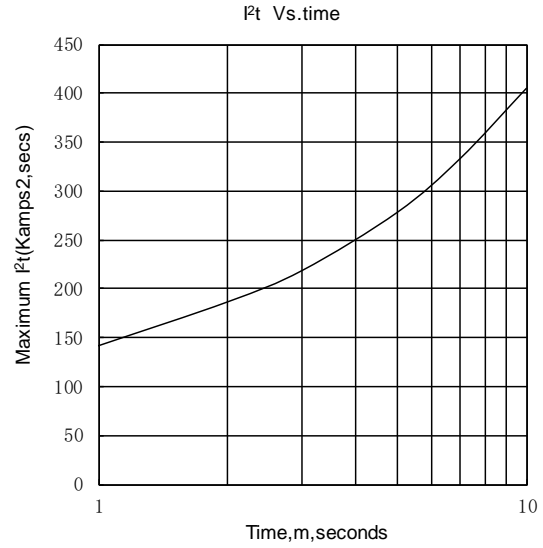


Fig.8

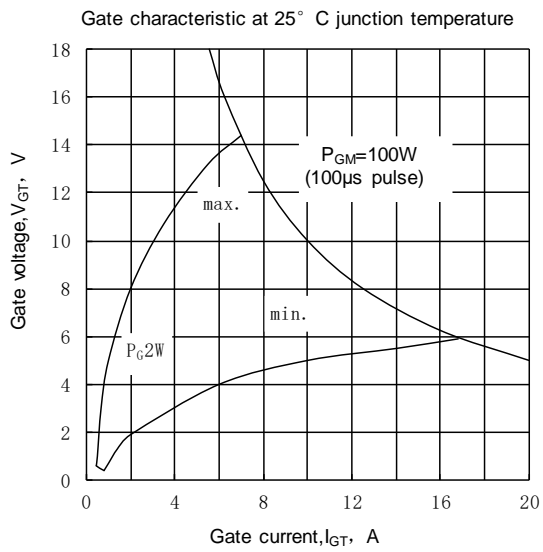


Fig.9

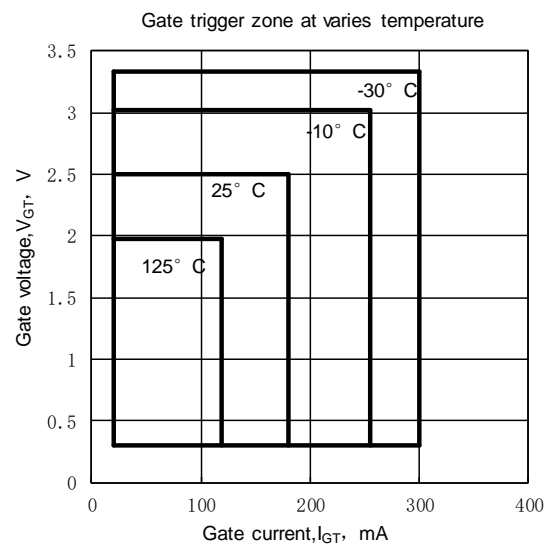


Fig.10

Outline:

